



Integrated Device Technology, Inc.
2975 Stender Way, Santa Clara, CA - 95054

PRODUCT/PROCESS CHANGE NOTICE (PCN)

PCN #: L0108-01R1 DATE: 12/10/01
Product Affected: IDTQS3VH125, IDTQS3VH126, IDTQS3VH257, IDTQS3VH2245, IDTQS32XVH2245, IDTQS34XVH2245
Date Effective: November 13, 2001

MEANS OF DISTINGUISHING CHANGED DEVICES:
Product Mark, Back Mark, Date Code, Other. Prefix "YQ", "ZQ" or "QC" to "Z"

Contact: Bimla Paul
Title: Q. A. Manager
Phone #: (408) 654-6419
Fax #: (408) 492-8362
E-mail: bimla.paul@idt.com

Attachment: Yes No
Samples: Available upon request

DESCRIPTION AND PURPOSE OF CHANGE:

- Die Technology
Wafer Fabrication Process
Assembly Process
Equipment
Material
Testing
Manufacturing Site
Data Sheet
Other
PCN addendum to correct PCN # L0108-01 for die revision details Die revision "XQ" should be replaced with "YQ" or "ZQ" as follow:
YQ: IDTQS3VH125, IDTQS3VH126
ZQ: IDTQS3VH257, IDTQS3VH2245, IDTQS32XVH2245, IDTQS34XVH2245
The PCN effectivity date is November 13, 2001 (same as the original PCN).

RELIABILITY/QUALIFICATION SUMMARY:

There will be no impact or effect on the product reliability. The qualification data is attached.

CUSTOMER ACKNOWLEDGMENT OF RECEIPT:

IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail to grant approval or request additional information. If IDT does not receive acknowledgement within 30 days of this notice it will be assumed that this change is acceptable. IDT reserves the right to ship either version manufactured after the process change effective date until the inventory on the earlier version has been depleted.

Customer:
Name/Date:
Title:
E-Mail Address:
Phone# /Fax# :

Approval for shipments prior to effective date.

CUSTOMER COMMENTS:

IDT ACKNOWLEDGMENT OF RECEIPT:

RECD. BY: DATE:



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ATTACHMENT - PCN #: L0108-01R1 (Addendum)

PCN Type: Die revision

Data Sheet Change No

Detail of Change The die has been revised from "YQ" , "ZQ" and "QC" stepping to "Z" stepping

Die Revision Details

	<u>Current Die Rev</u> YQ	<u>Current Die Rev</u> ZQ	<u>Current Die Rev</u> QC	<u>New Die Rev</u> Z
Wafer Fab Technology	0.8µm	0.8µm	0.8µm	0.8µm
Poly Gate	0.8µm	0.8µm	0.8µm	0.8µm
Minimum Gate Oxide Thickness	150Å	150Å	150Å	150Å
Wafer Size	6"	6"	6"	6"
Fab Facility	Fab 5 (PSA, Australia)	Fab 5 (PSA, Australia)	Fab 2 (Salinas, CA)	Fab 2 (Salinas, CA)
Date Code Prefix	YQ	ZQ	QC	Z
Affected Parts	IDTQS3VH125 IDTQS3VH126	IDTQS3VH257 IDTQS3VH2245 IDTQS32XH2245 IDTQS34XVH2245	IDTQS3VH125 IDTQS3VH126 IDTQS3VH257 IDTQS3VH2245 IDTQS32XVH2245 IDTQS34XVH2245	IDTQS3VH125 IDTQS3VH126 IDTQS3VH257 IDTQS3VH2245 IDTQS32XVH2245 IDTQS34XVH2245



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PRODUCT/PROCESS CHANGE NOTICE (PCN)
ATTACHMENT - PCN #: L0108-01R1 (Addendum)

Qualification Plan QLG-01-01

Test Vehicle: IDTQS3VH862

Qualification Test Plan and Results:

Test Description	SS/Acc #	Test Results
Dynamic High Temp Operating Life Test Mil-Std-883, Method-1005	116/0	116/0
ESD - HBM Mil-Std-883, Method-3015	3/0	3500 Volts
ESD-CDM JESD22-C101	3/0	1000 Volts
ESD-MM EIAJ-IC-121	3/0	400 Volts
Latch-up EIA/JESD78	10/0	10/0

Characterization Data:

Characterization data is available upon request.